

**DMP2225L**

**P-CHANNEL ENHANCEMENT MODE MOSFET**

**Product Summary**

$V_{(BR)DSS}$	$R_{DS(ON)}$	Package	$I_D$ $T_A = +25^\circ C$
-20V	110mΩ @ $V_{GS} = -4.5V$	SOT23	-2.6A
	225mΩ @ $V_{GS} = -2.5V$		-2.0A

**Description**

This new generation MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

**Applications**

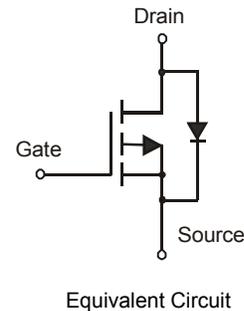
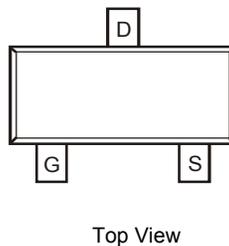
- General Purpose Interfacing Switch
- Power Management Functions

**Features**

- Low On-Resistance:
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)

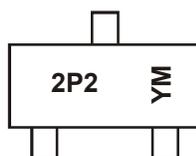


**Ordering Information**

Part Number	Qualification	Case	Packaging
DMP2225L-7	Commercial	SOT-23	3000/Tape & Reel
DMP2225LQ-7	Automotive	SOT-23	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.  
2. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

**Marking Information**



2P2 = Product Type Marking Code  
YM = Date Code Marking  
Y = Year (ex: V = 2008)  
M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

DMP2225L

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-20	V
Gate-Source Voltage			V <sub>GSS</sub>	±12	V
Continuous Drain Current (Note 5)	Stead State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-2.6 -2	A
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	8	A

**Thermal Characteristics**

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P <sub>D</sub>	1.08	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	R <sub>θJA</sub>	115	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-800	nA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
On-State Drain Current	I <sub>D(ON)</sub>	-6	—	—	A	V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -4.5V
		-3	—	—		V <sub>DS</sub> ≤ -5V, V <sub>GS</sub> = -2.5V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±80	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.45	—	-1.25	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	80	110	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -2.6A
		—	165	225		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2.0A
Forward Transfer Admittance	Y <sub>fs</sub>	—	4	—	S	V <sub>DS</sub> = -5V, I <sub>D</sub> = -2.6A
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	—	—	-1.26	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.6A
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>iss</sub>	—	250	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	88	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	58	—	pF	
Gate Resistance	R <sub>g</sub>	—	12	16	Ω	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	4.3	5.3	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -2.7A
Gate-Source Charge	Q <sub>gs</sub>	—	0.9	—		
Gate-Drain Charge	Q <sub>gd</sub>	—	2.1	—		

- Notes:
3. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  4. Repetitive rating, pulse width limited by junction temperature.
  5. Short duration pulse test used to minimize self-heating effect.